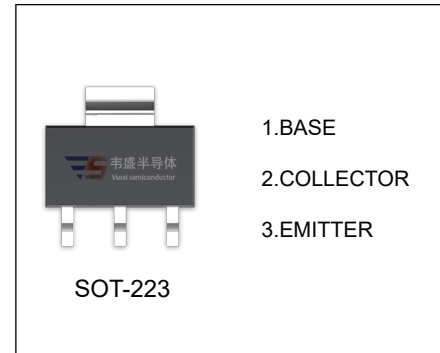


FZT692B TRANSISTOR (NPN)

FEATURES

- High Voltage
- Low saturation voltages



- 1.BASE
- 2.COLLECTOR
- 3.EMITTER

MAXIMUM RATINGS ($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	70	V
V_{CEO}	Collector-Emitter Voltage	70	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current	2.5	A
I_{CM}	Collector Current-Pulsed	5	A
P_C	Collector Power Dissipation	0.8	W
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	156	$^{\circ}\text{C}/\text{W}$
T_J, T_{stg}	Operation Junction and Storage Temperature Range	-55~+150	$^{\circ}\text{C}$

ELECTRICAL CHARACTERISTICS ($T_a=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-0.1\text{mA}, I_E=0$	70			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-10\text{mA}, I_B=0$	70			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-0.1\text{mA}, I_C=0$	5			V
Collector cut-off current	I_{CBO}	$V_{CB}=55\text{V}, I_E=0$			100	nA
Emitter cut-off current	I_{EBO}	$V_{EB}=4\text{V}, I_C=0$			100	nA
DC current gain	$h_{FE(1)}$	$V_{CE}=2\text{V}, I_C=100\text{mA}$	500			
	$h_{FE(2)}$	$V_{CE}=2\text{V}, I_C=500\text{mA}$	400			
	$h_{FE(3)}$	$V_{CE}=2\text{V}, I_C=1\text{A}$	150			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=100\text{mA}, I_B=0.5\text{mA}$			0.15	V
		$I_C=1\text{A}, I_B=10\text{mA}$			0.5	V
		$I_C=2\text{A}, I_B=200\text{mA}$			0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=1\text{A}, I_B=10\text{mA}$			0.9	V
Base-emitter voltage	V_{BE}	$V_{CE}=2\text{V}, I_C=1\text{A}$			0.9	V
Transition frequency	f_T	$V_{CE}=5\text{V}, I_C=200\text{mA}, f=1\text{MHz}$	10			MHz
Collector output capacitance	C_{ob}	$V_{CB}=20\text{V}, I_E=0, f=1\text{MHz}$		40		pF

Static Characteristic
